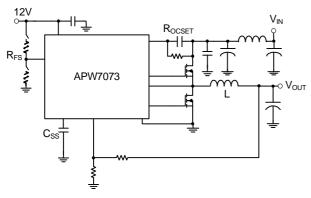


Synchronous Buck PWM Controller

Features

- · Single 12V Power Supply Required
- 0.6V Reference with 1% Accuracy
- Shutdown and Soft-Start Function
- Programmable Frequency Range from 50 kHz to 1000kHz
- · Voltage Mode PWM Control Design
- · Under-Voltage Protection (UVP)
- Over-Current Protection (OCP)
- SOP-14 Package
- Lead Free and Green Devices Available (RoHS Compliant)

Typical Application Circuit



General Description

The APW7073 is a voltage mode, synchronous PWM controller which drives dual N-channel MOSFETs. The device integrates all of the control, monitoring and protecting functions into a single package, provides one controlled power output with under-voltage and over-current protections.

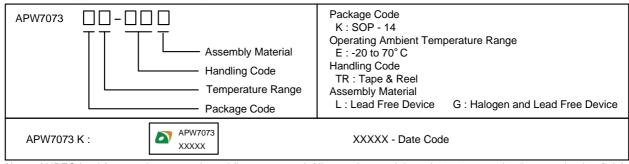
The APW7073 provides excellent regulation for output load variation. The internal 0.6V temperature-compensated reference voltage is designed to meet the requirement of low output voltage applications. The device includes a 200kHz free-running triangle-wave oscillator that is adjustable from 50kHz to 1000kHz.

The APW7073 has been equipped with excellent protection functions: POR, OCP, and UVP. The Power-On-Reset (POR) circuit can monitor the VCC, EN, and OCSET voltage to make sure the supply voltage exceeds their threshold voltage while the controller is running. The Over-Current Protection (OCP) monitors the output current by using the voltage drop across the upper MOSFET's $R_{DS(ON)}$. When the output current reaches the trip point, the controller will run the soft-start function until the fault events are removed. The Under-Voltage Protection (UVP) monitors the voltage at FB pin (V_{FB}) for short-circuit protection. When the V_{FB} is less than 50% of V_{REF} , the controller will shutdown the IC directly.

Applications

Graphic Cards

Ordering and Marking Information

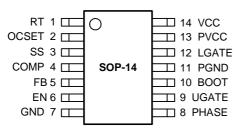


Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020C for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.



Pin Configuration



Absolute Maximum Ratings (Note 1)

Symbol	Parameter	Rating	Unit	
V _{CC} , V _{PVCC}	VCC, PVCC to GND	-0.3 to +16	V	
V _{BOOT} _V _{PHASE}	BOOT to PHASE	-0.3 to +16	V	
V _{BOOT}	BOOT to GND < 5ns pulse width	-0.3 to 32	V	
V _{UGATE}	UGATE to GND < 5ns pulse width	-0.3 to 32	V	
V V	UGATE to PHASE <400 ns pulse width	-5 to V _{BOOT} +5	V	
V _{UGATE} _V _{PHASE}	>400ns pulse width	-0.3 to V _{BOOT} +0.3	V	
V _{LGATE}	LGATE to PGND <400ns pulse width	-5 to V _{PVCC} +5	V	
V LGATE	>400ns pulse width	-0.3 to V _{PVCC} +0.3	V	
V	PHASE to GND <400ns pulse width	-10 to +30	V	
V _{PHASE}	>400ns pulse width	-0.3 to 16	V	
V _{RT} , V _{OCSET} , V _{EN}	RT, OCSET, EN to GND	-0.3 to V _{CC} +0.3	V	
$V_{FB_i}V_{COMP_i}V_{SS}$	FB, COMP, SS to GND	-0.3 to 7	V	
V _{PGND}	PGND to GND	-0.3 to +0.3	V	
TJ	Junction Temperature Range	-20 to 150	°C	
T _{STG}	Storage Temperature	-65 to 150	°C	
T _{SDR}	Maximum Lead Soldering Temperature, 10 Seconds	260	°C	

Note1: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Thermal Characteristics (Note 2,3)

Symbol	Parameter	Typical Value	Unit
θ_{JA}	Junction-to-Ambient Thermal Resistance in Free Air	160	°C/W
æ	Junction-to-Case Thermal Resistance in Free Air	25	°C/W

Note2: θ_{JA} is measured with the component mounted on a high effective the thermal conductivity test board in free air. Note 3: The case temperature is measured at the center of the exposed pad on the underside of the SOP-14 package.

Recommended Operating Conditions

Symbol	Parameter	Rating	Unit
V _{CC} , V _{PVCC}	IC Supply Voltage	10.8 to 13.2	V
V _{IN}	Converter Input Voltage	2.2 to 13.2	V
V _{OUT}	Converter Output Voltage	0.6 to V _{IN} x90%	V
lout	Converter Output Current	0 to 30	A
T _A	Ambient Temperature Range	-20 to 70	∞
T _J	Junction Temperature Range	-20 to 125	∞



Electrical Characteristics

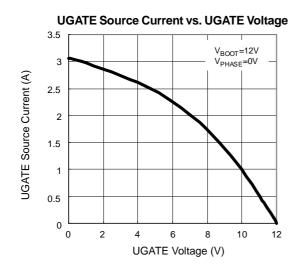
Unless otherwise specified, these specifications apply over V_{cc} =12V, and T_A =-20~70°C. Typical values are at T_A =25°C.

Symbol	Parameter	Test Conditions		APW7073	3	Unit
Symbol	Faranteter	rest Conditions	Min.	Тур.	Max.	Oill
INPUT SU	PPLY CURRENT					
Ι _{cc}	VCC Supply Current (Shutdown Mode)	UGATE, LGATE and EN = GND	-	0.5	1	mA
¹0C	VCC Supply Current	UGATE and LGATE Open	-	5	10	mΑ
POWER-O	N-RESET					
	Rising VCC Threshold		9	9.5	10.0	٧
	Falling VCC Threshold		7.5	8	8.5	V
	Rising V _{OCSET} Threshold		-	1.3	-	V
	VOCSET Hysteresis Voltage		-	0.1	-	٧
	Rising EN threshold Voltage		-	1.3	-	٧
	EN Hysteresis Voltage		-	0.1	-	٧
OSCILLAT	OR					
	Accuracy		-15	-	+15	%
Fosc	Free Running Frequency	RT = open	-	200	-	kHz
	Adjustment Range	RT pin: resistor to GND; Resistor to VCC	50	-	1000	kHz
Vosc	Ramp Amplitude	(nominal 1.35V to 2.95V)	-	1.6	-	V
Duty	Duty Cycle Range		0	-	90	%
REFEREN	CE		,	•		
V_{REF}	Reference Voltage		-	0.60	-	V
	Reference Voltage Tolerance		-1	-	+1	%
PWM ERR	OR AMPLIFIER		<u>'</u>	•		
Gain	Open Loop Gain	$R_L = 10k, C_L = 10pF^{(Note 4)}$	-	88	-	dB
GBWP	Open Loop Bandwidth	$R_L = 10k, C_L = 10pF^{(Note 4)}$	-	15	-	MHz
SR	Slew Rate	$R_L = 10k, C_L = 10pF^{(Note 4)}$	-	6	-	V/us
	FB Input Current	V _{FB} = 0.6V	-	0.1	1	μΑ
V _{COMP}	COMP High Voltage		-	5.5	-	V
V_{COMP}	COMP Low Voltage		-	0	-	V
I _{COMP}	COMP Source Current	V _{COMP} = 2V	-	5	-	mA
I _{COMP}	COMP Sink Current	V _{COMP} = 2V	-	5	-	mA
GATE DRI	VERS		'			
I _{UG ATE}	Upper Gate Source Current	V _{BOOT} = 12V, V _{UGATE} -V _{PHASE} = 2V	-	2.6	-	Α
R _{UGATE}	Upper Gate Sink Impedance	V _{BOOT} = 12V, I _{UGATE} = 0.1A	-	1.6	2.4	Ω
I _{LG ATE}	Lower Gate Source Current	V _{PVCC} = 12V, V _{LGATE} = 2V	-	4.9	-	Α
R _{LGATE}	Lower Gate Sink Impedance	V _{PVCC} = 12V, I _{LGATE} = 0.1A	-	1.25	1.88	Ω
T _D	Dead Time		-	20	-	nS
PROTECT		1		1	1	
	FB Under Voltage Level	Percent of V _{REF}	45	50	55	%
I _{OCSET}	OCSET Source Current	V _{OCSET} = 11.5V	170	200	250	μΑ
	SOFT-START	1		1		•
I _{SS}	Soft-Start Charge Current		24	30	36	μΑ
-33						٠ سم

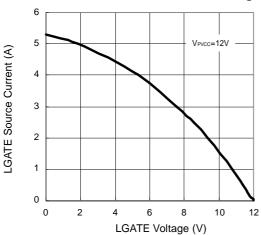
Note 4 : Guaranteed by design



Typical Operating Characteristics







Switching Frequency vs.

Junction Temperature

205

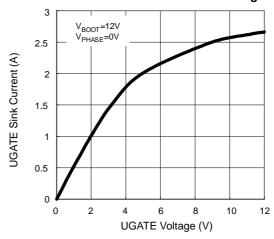
195

190

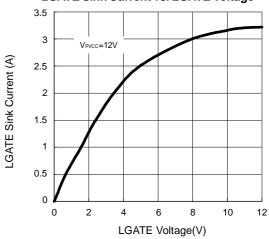
-40 -20 0 20 40 60 80 100 120

Junction Temperature (°C)

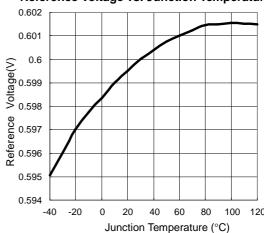
UGATE Sink Current vs. UGATE Voltage



LGATE Sink Current vs. LGATE Voltage



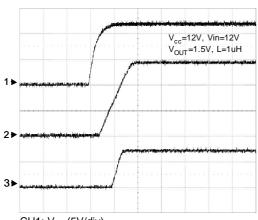
Reference Voltage vs. Junction Temperature





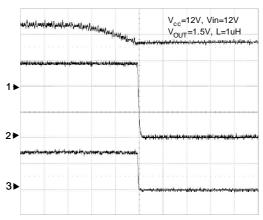
Operating Waveforms

Power On



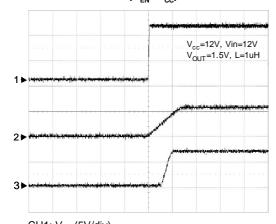
CH1: $V_{\rm CC}$ (5V/div) CH2: $V_{\rm SS}$ (2V/div) CH3: $V_{\rm OUT}$ (1V/div) Time: 10ms/div

Power Off



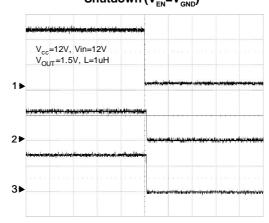
CH1: V_{CC} (5V/div) CH2: V_{SS} (2V/div) CH3: V_{OUT} (1V/div) Time: 2ms/div

$EN(V_{EN}=V_{CC})$



CH1: V_{EN} (5V/div) CH2: V_{SS} (5V/div) CH3: V_{OUT} (1V/div) Time: 10ms/div

Shutdown ($V_{EN} = V_{GND}$)

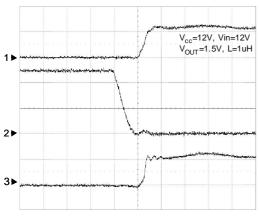


CH1: V_{EN} (5V/div) CH2: V_{SS} (5V/div) CH3: V_{OUT} (1V/div) Time: 10ms/div



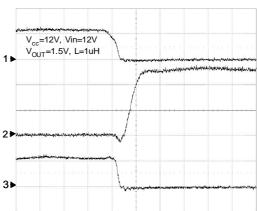
Operating Waveforms (Cont.)





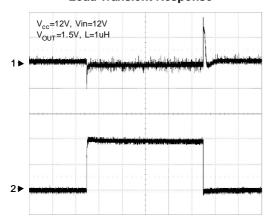
 $\begin{array}{ll} \text{CH1: V}_{\text{UGATE}}\left(20\text{V/div}\right) \\ \text{CH2: V}_{\text{LGATE}}\left(5\text{V/div}\right) \\ \text{CH3: V}_{\text{PHASE}}\left(10\text{V/div}\right) \\ \text{Time: 50ns/div} \end{array}$

UGATE Falling



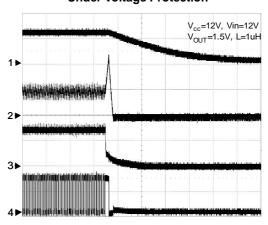
 $\begin{array}{ll} \text{CH1: V}_{\text{UGATE}} \left(20\text{V/div} \right) \\ \text{CH2: V}_{\text{LGATE}} \left(5\text{V/div} \right) \\ \text{CH3: V}_{\text{PHASE}} \left(10\text{V/div} \right) \\ \text{Time: 50ns/div} \end{array}$

Load Transient Response



CH1: V_{OUT} (500mV/div) CH4: I_{OUT} (5A/div) Time: 200us/div

Under Voltage Protection

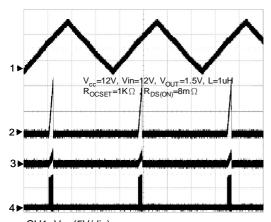


CH1: V_{SS} (5V/div) CH2: I_{OUT} (5A/div) CH3: V_{OUT} (1V/div) CH4: V_{UGATE} (10V/div) Time: 10ms/div



Operating Waveforms (Cont.)

Over Current Protection



CH1: $V_{\rm SS}$ (5V/div) CH2: IL (10A/div) CH3: $V_{\rm OUT}$ (1V/div) CH4: $V_{\rm UGATE}$ (20V/div) Time: 10ms/div

V_{cc}=12V, Vin=12V V_{OUT}=1.5V, L=1uH

Short Test

CH1: V_{SS} (5V/div) CH2: IL (10A/div) CH3: V_{OUT} (1V/div) CH4: V_{UGATE} (20V/div) Time: 10ms/div



Function Pin Description

VCC

Power supply input pin. Connect a nominal 12V power supply to this pin. The power-on-reset function monitors the input voltage by this pin. It is recommended that a decoupling capacitor (1 to $10\mu F$) be connected to the GND for noise decoupling.

PVCC

This pin provides a supply voltage for the lower gate drive, connect this pin to the VCC pin in normal use.

BOOT

This pin provides the bootstrap voltage to the upper gate driver for driving the N-channel MOSFET.

PHASE

This pin is the return path for the upper gate driver. Connect this pin to the upper MOSFET source. This pin is also used to monitor the voltage drop across the MOSFET for over-current protection.

GND

This pin is the signal ground pin. Connect the GND pin to a good ground plane.

PGND

This pin is the power ground pin for the lower gate driver. It should be tied to the GND pin on the board.

COMP

This pin is the output of PWM error amplifier. It is used to set the compensation components.

FΒ

This pin is the inverting input of the PWM error amplifier. It is used to set the output voltage and the compensation components. This pin is also monitored for undervoltage protection. If the FB voltage is under 50% of reference voltage, the device will be shut down.

UGATE

This pin is the gate driver for the upper MOSFET of PWM output.

LGATE

This pin is the gate driver for the lower MOSFET of PWM output.

SS

Connect a capacitor to the GND and a $30\mu A$ current source charges this capacitor to set the soft-start time.

OCSET

This pin serves two functions: a shutdown control and the setting of over current limit threshold. Pulling this pin below 1.3V will shutdown the controller, forcing the UGATE and LGATE signals to be low.

A resistor (Rocset) connected between this pin and the drain of the high side MOSFET will determine the over current limit. An internal 200 μ A current source will flow through this resistor, creating a voltage drop, which will be compared with the voltage across the high side MOSFET. The threshold of the over current limit is therefore given by:

$$I_{PEAK} = \frac{I_{OCSET}(200uA) \times R_{OCSET}}{R_{DS(ON)}}$$

EN

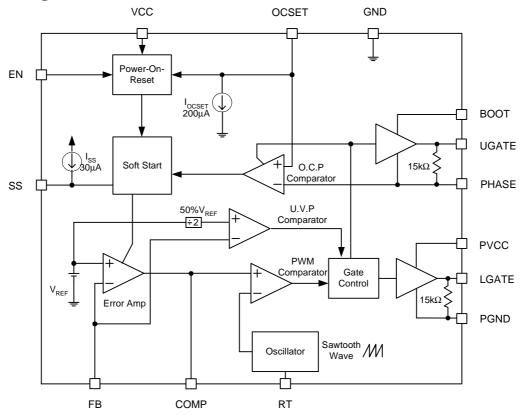
Pull this pin above 1.3V to enable the device and pull this pin below 1.2V to disable the device. In shutdown, the SS is discharged and the UGATE and LGATE pins are held low. Note that don't leave this pin open.

RT

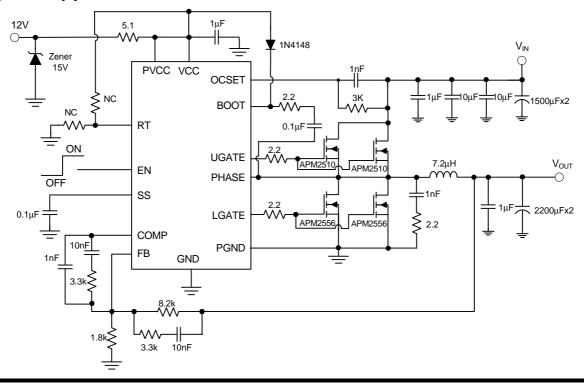
This pin allows adjusting the switching frequency. Connect a resistor from RT pin to the ground to increase the switching frequency. Conversely, connect a resistor from RT to the VCC to decrease the switching frequency.



Block Diagram



Typical Application Circuit





Function Description

Power-On-Reset (POR)

The Power-On-Reset (POR) function of APW7073 continually monitors the input supply voltage ($V_{\rm CC}$), the enable (EN) pin, and OCSET pin. The supply voltage ($V_{\rm CC}$) must exceed its rising POR threshold voltage. The voltage at OCSET pin is equal to $V_{\rm IN}$ less a fixed voltage drop ($V_{\rm OCSET} = V_{\rm IN}^- V_{\rm ROCSET}$). EN pin can be pulled high with connecting a resistor to VCC. The POR function initiates soft-start operation after VCC, EN, and OCSET voltages exceed their POR thresholds. For operation with a single +12V power source, $V_{\rm IN}$ and $V_{\rm cc}$ are equivalent and the +12V power source must exceed the rising VCC threshold. The POR function inhibits operation at disabled status (EN pin low). With both input supplies above their POR thresholds, the device initiates a soft-start interval.

Soft-Start/EN

The SS/EN pins control the soft-start and enable or disable the controller. Connect a soft-start capacitor from SS pin to GND to set the soft-start interval. Figure 1. shows the soft-start interval. When $V_{\rm CC}$ reaches its Power-On-Reset threshold (9.5V), internal $30\mu{\rm A}$ current source starts to charge the capacitor. When the $V_{\rm SS}$ reaches the enabled threshold about 1.8V, the internal 0.6V reference starts to rise and follow the $V_{\rm SS}$; the error amplifier output ($V_{\rm COMP}$) suddenly raises to 1.35V, which is the valley of the triangle wave of the oscillator, leads the $V_{\rm OUT}$ to start-up. Until the $V_{\rm SS}$ reaches about 4.2V, the internal reference completes the soft-start interval and reaches to 0.6V; and then the $V_{\rm OUT}$ is in regulation. The SS still rises to 5.5V and then stops.

$$T_{Soft-Start} = t_2 - t_1 = \frac{C_{SS}}{I_{SS}} \cdot 2.4V$$

Where:

 C_{SS} = external Soft-Start capacitor I_{SS} = Soft-Start current=30 μ A

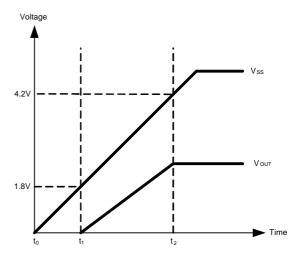


Figure 1. Soft-Start Internal

Over-Current Protection (monitor upper MOSFET)

The APW7073 monitors the voltage across the upper MOSFET and uses the OCSET pin to set the over-current trip point.

A resistor ($R_{\rm OCSET}$) connected between OCSET pin and the drain of the upper MOSFET will determine the over current limit. An internal 200 μ A current source will flow through this resistor, creating a voltage drop, which will be compared with the voltage across the upper MOSFET. When the voltage across the upper MOSFET exceeds the voltage drop across the $R_{\rm OCSET}$, an over-current will be detected. The threshold of the over current limit is therefore given by:

$$I_{\text{LIMIT}} = \frac{I_{\text{OCSET}} \times R_{\text{OCSET}}}{R_{\text{DS(ON)}}}$$

For the over-current is never occurred in the normal operating load range; the variation of all parameters in the above equation should be determined.

- The MOSFET's $R_{\mathrm{DS(ON)}}$ is varied by temperature and gate to source voltage, the user should determine the maximum $R_{\mathrm{DS(ON)}}$ in manufacturer's datasheet.
- The minimum I_{OCSET} (170 $\mu A)$ and minimum R_{OCSET} should be used in the above equation.
- Note that the I_{LIMIT} is the current flow through the upper MOSFET; I_{LIMIT} must be greater than maximum output current add the half of inductor ripple current.



Function Description (Cont.)

Over-Current Protection (Cont.)

An over current condition will shut down the device and discharge the $C_{\rm ss}$ with a $30\mu A$ sink current and then initiates the soft-start sequence. If the over current condition is not removed during the soft-start interval, the device will be shut down while the over current is detected and the $V_{\rm ss}$ still rises to 4V to complete its cycle. The soft-start function will be cycled until the over current condition is removed. Both over-current protections have the same behavior while an over current condition is detected.

Under-Voltage Protection

The FB pin is monitored during converter operation by their own Under Voltage (UV) comparator. If the FB voltage drops below 50% of the reference voltage (50% of 0.6V = 0.3V), a fault signal is internally generated, and the device turns off both high-side and low-side MOSFET and the converter's output is latched to be floating.

Switching Frequency

The APW7073 provides the oscillator switching frequency adjustment. The device includes a 200kHz free-running triangle wave oscillator. If operating in higher frequency than 200kHz, connect a resistor from RT pin to the ground to increase the switching frequency. Conversely, if operating in lower frequency than 200kHz, connect a resistor from RT to the VCC to decrease the switching frequency.

Figure 2. shows how to select the resistor for the desired frequency. Figure 3. shows more detail for the higher frequencies and Figure 4 shows the lower frequency detail.

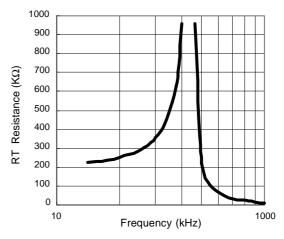


Figure 2. Oscillator Frequency vs. RT Resistance

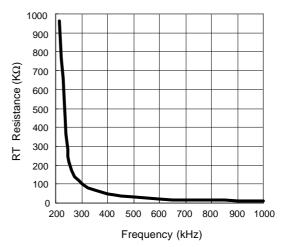


Figure 3. Oscillator Frequency vs. RT Resistance (High Frequency)

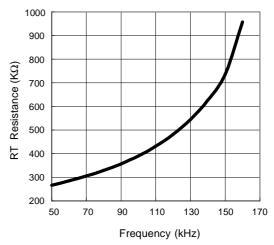


Figure 4. Oscillator Frequency vs. RT Resistance (Low Frequency)



Application Information

Output Voltage Selection

The output voltage can be programmed with a resistive divider. Use 1% or better resistors for the resistive divider is recommended. The FB pin is the inverter input of the error amplifier, and the reference voltage is 0.6V. The output voltage is determined by:

$$V_{OUT} = 0.6 \times \left(1 + \frac{R_{OUT}}{R_{GND}}\right)$$

Where $R_{\rm OUT}$ is the resistor connected from $V_{\rm OUT}$ to FB and $R_{\rm GND}$ is the resistor connected from FB to the GND.

Output Inductor Selection

The inductor value determines the inductor ripple current and affects the load transient response. Higher inductor value reduces the inductor's ripple current and induces lower output ripple voltage. The ripple current and ripple voltage can be approximated by:

$$I_{RIPPLE} = \frac{V_{IN} - V_{OUT}}{F_{S} \times L} \times \frac{V_{OUT}}{V_{IN}}$$

$$\Delta V_{OUT} = I_{RIPPLF} \times ESR$$

where Fs is the switching frequency of the regulator.

Although increase of the inductor value and frequency reduces the ripple current and voltage, a tradeoff will exist between the inductor's ripple current and the regulator load transient response time.

A smaller inductor will give the regulator a faster load transient response at the expense of higher ripple current. Increasing the switching frequency (F_s) also reduces the ripple current and voltage, but it will increase the switching loss of the MOSFET and the power dissipation of the converter. The maximum ripple current occurs at the maximum input voltage. A good starting point is to choose the ripple current to be approximately 30% of the maximum output current. Once the inductance value has been chosen, select an inductor is capable of carrying the required peak current without going into saturation. In some types of inductors, especially core that is made of ferrite, the ripple current will increase abruptly when it saturates. This will result in a larger output ripple voltage.

Output Capacitor Selection

Higher capacitor value and lower ESR reduce the output ripple and the load transient drop. Therefore, selecting high performance low ESR capacitors is intended for switching regulator applications. In some applications, multiple capacitors have to be parallel to achieve the desired ESR value. A small decoupling capacitor in parallel for bypassing the noise is also recommended, and the voltage rating of the output capacitors also must be considered. If tantalum capacitors are used, make sure they are surge tested by the manufactures. If in doubt, consult the capacitors manufacturer.

Input Capacitor Selection

The input capacitor is chosen based on the voltage rating and the RMS current rating. For reliable operation, select the capacitor voltage rating to be at least 1.3 times higher than the maximum input voltage. The maximum RMS current rating requirement is approximately $I_{\text{OUT}}/2$, where I_{OUT} is the load current. During power up, the input capacitors have to handle large amount of surge current. If tantalum capacitors are used, make sure they are surge tested by the manufactures. If in doubt, consult the capacitors manufacturer. For high frequency decoupling, a ceramic capacitor $1\mu\text{F}$ can be connected between the drain of upper MOSFET and the source of lower MOSFET.

MOSFET Selection

The selection of the N-channel power MOSFETs are determined by the $R_{DS(ON)}$, reverse transfer capacitance (C_{RSS}) and maximum output current requirement. There are two components of loss in the MOSFETs: conduction loss and transition loss. For the upper and lower MOSFET, the losses are approximately given by the following equations:

$$\begin{split} &P_{_{UPPER}} = I_{_{OUT}}^{2}(1+TC)(R_{_{DS(ON)}})D + (0.5)(I_{_{OUT}})(V_{_{IN}})(t_{_{SW}})F_{_{S}} \\ &P_{_{LOWER}} = I_{_{OUT}}^{2}(1+TC)(R_{_{DS(ON)}})(1-D) \end{split}$$

Where I_{OUT} is the load current

TC is the temperature dependency of $R_{DS(ON)}$

F_s is the switching frequency

t_{sw} is the switching interval

D is the duty cycle



Application Information (Cont.)

MOSFET Selection (Cont.)

Note that both MOSFETs have conduction loss while the upper MOSFET includes an additional transition loss. The switching internal, t_{SW} , is the function of the reverse transfer capacitance $C_{\text{RSS}}.$ The (1+TC) term is to factor in the temperature dependency of the $R_{\text{DS(ON)}}$ and can be extracted from the " $R_{\text{DS(ON)}}$ vs Temperature" curve of the power MOSFET.

PWM Compensation

The output LC filter of a step down converter introduces a double pole, which contributes with -40dB/decade gain slope and 180 degrees phase shift in the control loop. A compensation network among COMP, FB, and $V_{\rm OUT}$ should be added. The compensation network is shown in Figure 8. The output LC filter consists of the output inductor and output capacitors. The transfer function of the LC filter is given by:

$$F_{ESR} = \frac{1}{2 \times \pi \times ESR \times C_{OUT}}$$

The F_{LC} is the double poles of the LC filter, and F_{ESR} is the zero introduced by the ESR of the output capacitor.

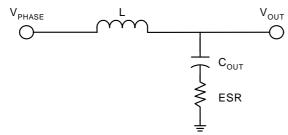


Figure 5. The Output LC Filter

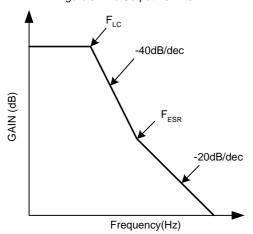


Figure 6. The LC Filter GAIN and Frequency

The PWM modulator is shown in Figure 7. The input is the output of the error amplifier and the output is the PHASE node. The transfer function of the PWM modulator is given by:

$$GAIN_{PWM} = \frac{V_{IN}}{\Delta V_{OSC}}$$

$$V_{OSC}$$

$$V_{OSC}$$

$$V_{OSC}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OUTPUT}$$

$$V_{OSC}$$

$$V_{OUTPUT}$$

$$V_{OU$$

Figure 7. The PWM Modulator

Driver

Error Amplifier

The compensation network is shown in Figure 8. It provides a close loop transfer function with the highest zero crossover frequency and sufficient phase margin. The transfer function of error amplifier is given by:

$$\begin{split} & \mathsf{GAIN}_{\mathsf{AMP}} = \frac{V_{\mathsf{COMP}}}{V_{\mathsf{OUT}}} = \frac{\frac{1}{\mathsf{sC1}} /\! \left(\mathsf{R2} + \frac{1}{\mathsf{sC2}} \right)}{\mathsf{R1} /\! \left(\mathsf{R3} + \frac{1}{\mathsf{sC3}} \right)} \\ & = \frac{\mathsf{R1} \! + \! \mathsf{R3}}{\mathsf{R1} \! \times \! \mathsf{R3} \! \times \! \mathsf{C1}} \! \times \! \frac{\left(\mathsf{s} + \frac{1}{\mathsf{R2} \! \times \! \mathsf{C2}} \right) \! \times \! \left(\mathsf{s} + \frac{1}{(\mathsf{R1} \! + \! \mathsf{R3}) \! \times \! \mathsf{C3}} \right)}{\mathsf{s} \! \left(\mathsf{s} + \frac{\mathsf{C1} \! + \! \mathsf{C2}}{\mathsf{R2} \! \times \! \mathsf{C1} \! \times \! \mathsf{C2}} \right) \! \times \! \left(\mathsf{s} + \frac{1}{\mathsf{R3} \! \times \! \mathsf{C3}} \right)} \end{split}$$

The poles and zeros of the transfer function are:

Figure 8. Compensation Network



Application Information (Cont.)

PWM Compensation (Cont.)

The closed loop gain of the converter can be written as:

$$GAIN_{LC}XGAIN_{PWM}XGAIN_{AMP}$$

Figure 9. shows the asymptotic plot of the closed loop converter gain, and the following guidelines will help to design the compensation network. Using the below guidelines should give a compensation similar to the curve plotted. A stable closed loop has a -20dB/ decade slope and a phase margin greater than 45 degree.

- 1. Choose a value for R1, usually between 1K and 5K.
- 2. Select the desired zero crossover frequency

$$F_0$$
: (1/5 ~ 1/10) X $F_s > F_0 > F_{ESR}$

Use the following equation to calculate R2:

$$R2 = \frac{\Delta V_{OSC}}{V_{IN}} \times \frac{F_{O}}{F_{LC}} \times R1$$

3. Place the first zero $\rm F_{z_1}$ before the output LC filter double pole frequency $\rm F_{LC}$.

$$F_{71} = 0.75 \text{ X } F_{10}$$

Calculate the C2 by the equation:

$$C2 = \frac{1}{2 \times \pi \times R2 \times F_{LC} \times 0.75}$$

Set the pole at the ESR zero frequency F_{ESR}:

$$F_{P1} = F_{ESR}$$

Calculate the C1 by the equation:

$$C1 = \frac{C2}{2 \times \pi \times R2 \times C2 \times F_{ESR} - 1}$$

5. Set the second pole F_{P2} at the half of the switching frequency and also set the second zero F_{Z2} at the output LC filter double pole F_{LC} . The compensation gain should not exceed the error amplifier open loop gain, check the compensation gain at F_{P2} with the capabilities of the error amplifier.

$$F_{P2} = 0.5 \text{ X } F_{S}$$

$$F_{79} = F_{10}$$

Combine the two equations will get the following component calculations:

$$GAIN_{LC} = \frac{1 + s \times ESR \times C_{OUT}}{s^2 \times L \times C_{OUT} + s \times ESR \times C_{OUT} + 1}$$

The poles and zero of this transfer functions are:

$$\begin{aligned} F_{LC} &= \frac{1}{2 \times \pi \times \sqrt{L \times C_{OUT}}} \\ R3 &= \frac{R1}{\frac{F_S}{2 \times F_{LC}} - 1} \\ C3 &= \frac{1}{\pi \times R3 \times F_S} \end{aligned}$$

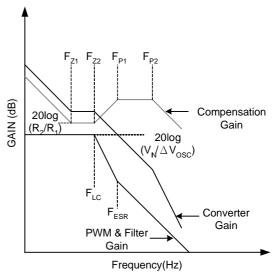


Figure 9. Converter Gain and Frequency



Layout Consideration

Layout Consideration

In any high switching frequency converter, a correct layout is important to ensure proper operation of the regulator. With power devices switching at 300kHz, the resulting current transient will cause voltage spike across the interconnecting impedance and parasitic circuit elements. As an example, consider the turn-off transition of the PWM MOSFET. Before turn-off, the MOSFET is carrying the full load current. During turn-off, current stops flowing in the MOSFET and is free-wheeling by the lower MOSFET and parasitic diode. Any parasitic inductance of the circuit generates a large voltage spike during the switching interval. In general, using short and wide printed circuit traces should minimize interconnecting impedances and the magnitude of voltage spike. And signal and power grounds are to be kept separating till combined using the ground plane construction or single point grounding. Figure 10 illustrates the layout, with bold lines indicating high current paths; these traces must be short and wide. Components along the bold lines should be placed lose together. Below is a checklist for your layout:

- Keep the switching nodes (UGATE, LGATE, and PHASE) away from sensitive small signal nodes since these nodes are fast moving signals. Therefore, keep traces to these nodes as short as possible.
- The traces from the gate drivers to the MOSFETs (UGATE, LGATE) should be short and wide.
- Place the source of the high-side MOSFET and the drain of the low-side MOSFET as close as possible. Minimizing the impedance with wide layout plane between the two pads reduces the voltage bounce of the node.
- Decoupling capacitor, compensation component, the resistor dividers, boot capacitors, and SS capacitors should be close their pins. (For example, place the decoupling ceramic capacitor near the drain of the high-side MOSFET as close as possible. The bulk capacitors are also placed near the drain).
- The input capacitor should be near the drain of the upper MOSFET; the output capacitor should be near

the loads. The input capacitor GND should be close to the output capacitor GND and the lower MOSFET GND.

- The drain of the MOSFETs ($V_{\rm IN}$ and PHASE nodes) should be a large plane for heat sinking.

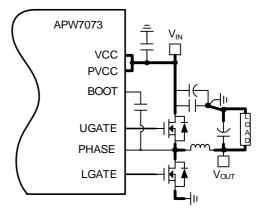
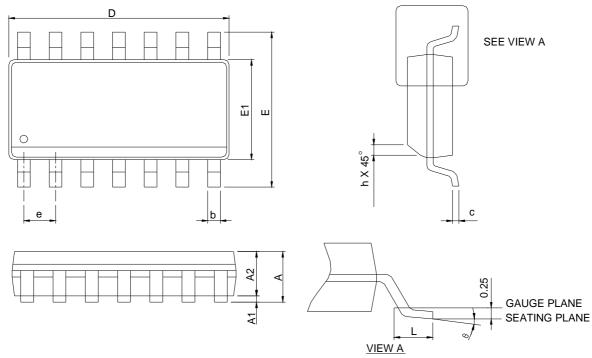


Figure 10. Layout Guidelines



Package Information

SOP-14



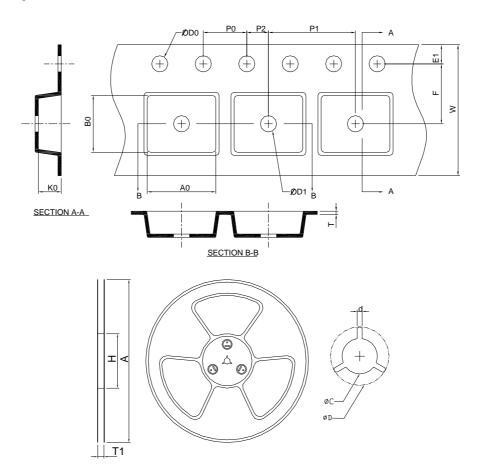
S		SOP-14				
SYMBOL	MILLIM	ETERS	INCHES			
O L	MIN.	MAX.	MIN.	MAX.		
Α		1.75		0.069		
A1	0.10	0.25	0.004	0.010		
A2	1.25		0.049			
b	0.31	0.51	0.012	0.020		
С	0.17	0.25	0.007	0.010		
D	8.55	8.75	0.337	0.344		
Е	5.80	6.20	0.228	0.244		
E1	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.05	0 BSC		
h	0.25	0.50	0.010	0.020		
L	0.40	1.27	0.016	0.050		
θ	0°	8°	0°	8°		

Note: 1. Follow JEDEC MS-012 AB.

- 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
- 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.



Carrier Tape & Reel Dimensions



Application	Α	Н	T1	С	d	D	W	E1	F
	330.0±2.00	50 MIN.	16.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	16.0±0.30	1.75±0.10	7.50±0.10
SOP-14	P0	P1	P2	D0	D1	Т	A0	В0	K0
	4.0±0.10	8.0±0.10	2.0±0.10	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40±0.20	9.00±0.20	2.10±0.20

(mm)

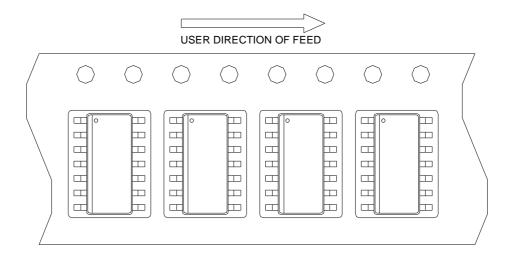
Devices Per Unit

Package Type	Unit	Quantity
SOP- 14	Tape & Reel	2500

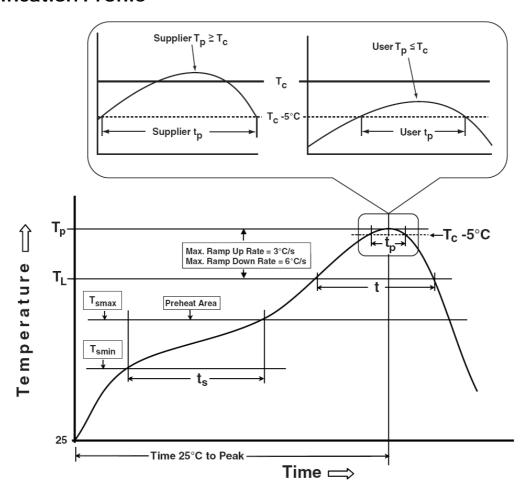


Taping Direction Information

SOP-14



Classification Profile





Classification Reflow Profiles

Pb-Free Assembly
150 °C 200 °C 60-120 seconds
3°C/second max.
217 °C 60-150 seconds
Classification Temp in table 2
30** seconds
6 °C/second max.
8 minutes max.

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package	Volume mm ³	Volume mm ³
Thickness	<350	³ 350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	<350	350-2000	>2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ Tj=125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C
НВМ	MIL-STD-883-3015.7	VHBM≥2KV
MM	JESD-22, A115	VMM≧200V
Latch-Up	JESD 78	10ms, 1 _{tr} ≥100mA

^{**} Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.



Customer Service

Anpec Electronics Corp.

Head Office:

No.6, Dusing 1st Road, SBIP, Hsin-Chu, Taiwan, R.O.C. Tel: 886-3-5642000 Fax: 886-3-5642050

Taipei Branch:

2F, No. 11, Lane 218, Sec 2 Jhongsing Rd., Sindian City, Taipei County 23146, Taiwan

Tel: 886-2-2910-3838 Fax: 886-2-2917-3838